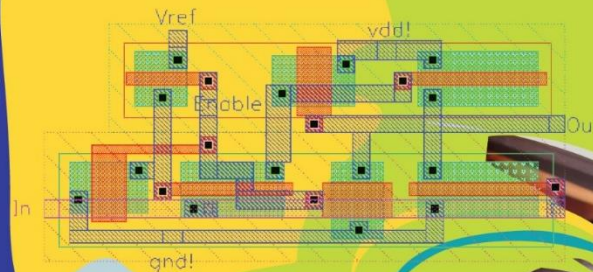


# Logical Effort

## Advanced Digital IC Design



Lecture

5

Khosrow Ghadiri





- **Logic effort** is an assignment of a number to logic gate to describe the drive strength (current) of the gate relative to that of a reference inverter.
- A logic gate is characterized by:
  - Logical effort
  - Parasitic delay
- Logic effort definitions:
- **1** Measure of how much worse the gate ability to deliver output current compare with an inverter with identical input capacitance
- **2** The ratio of gate input capacitance to that of an inverter which deliver equal output current.
- **3** The slope of the gate input capacitance vs. fanout curve divided by the slope of an inverter delay vs. fanout curve



- The Logical effort of an input group  $g_A$

$$g_A = \frac{C_A}{C_{inv}} = \frac{\sum_i^A C_i}{C_{inv}}$$

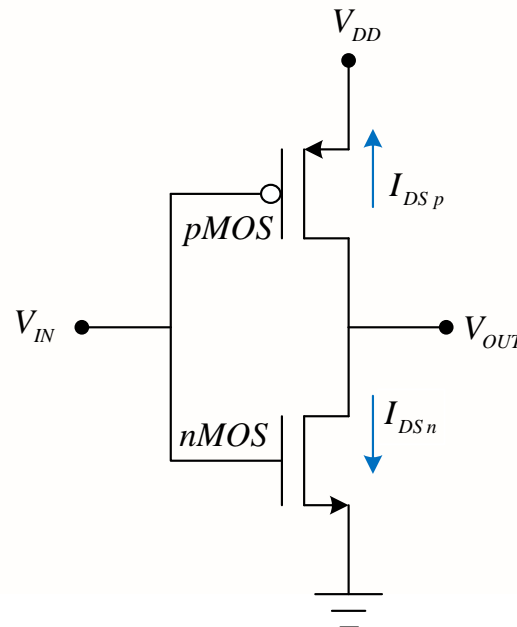
- The capacitance  $C_A$  is combined input capacitance of every signal in the input group A.
- The capacitance  $C_{inv}$  is input capacitance of inverter designed to have the same drive capability of the digital gate.
- Assumption: mobility of pMOS is half of the nMOS

$$\gamma = \mu = \frac{\mu_n}{\mu_p}$$

- Capacitance is proportional to the width W.
- The conductance is proportional to the width W.



- The Inverter input low and output high.
- The mobility of pMOS is half of nMOS.
- Pullup input capacitance of an inverter is proportion to  $2W$
- Pulldown input capacitance of an inverter is proportion to  $W$
- Total input capacitance of an inverter is proportion to  $3W$





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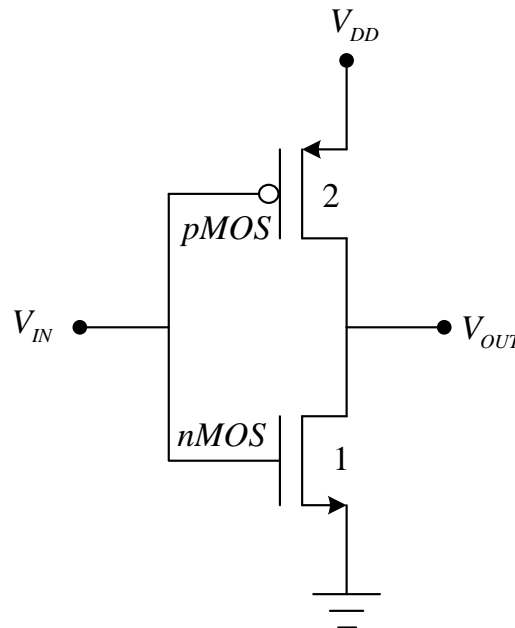
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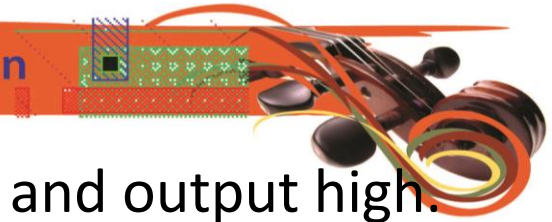
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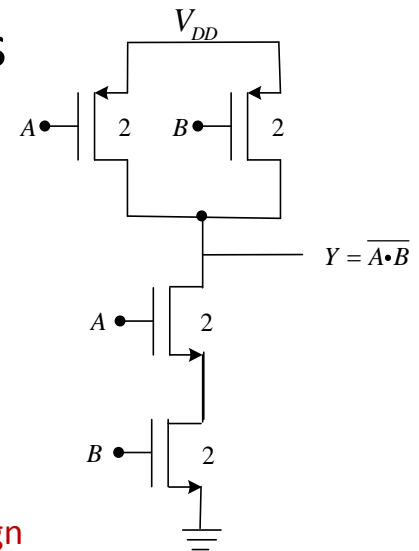


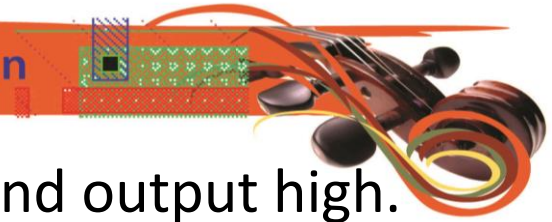


- The 2-input NAND gate with two inputs low and output high.
- The mobility of pMOS is half of nMOS.
- Pullup input capacitance of an inverter is proportion to  $2W$
- Pulldown input capacitance of an inverter is proportion to  $2W$
- the input capacitance of one input signal of 2-input NAND gate is proportion to the sum of the width of pullup transistors and pulldown transistors  $2W + 2W = 4W$
- Total input capacitance of an inverter is proportion to  $3W$
- The two pulldown transistors are in series

- The two pullup transistors are in parallel

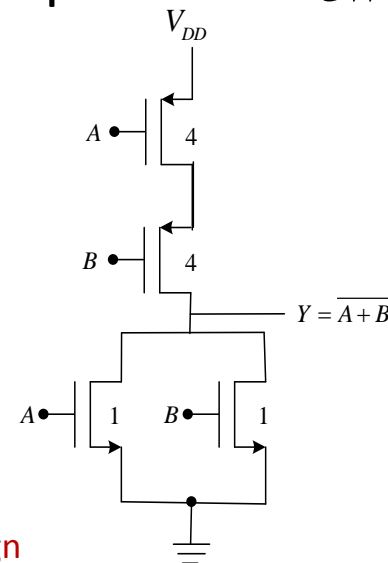
- The logical effort  $g_{NAND} = \frac{C_{NAND}}{C_{inv}} = \frac{4}{3}$





- The 2-input NOR gate with two inputs low and output high.
- The mobility of pMOS is half of nMOS.
- Pullup input capacitance of an inverter is proportion to  $2W$
- Pulldown input capacitance of an inverter is proportion to  $2W$
- the input capacitance of one input signal of 2-input NOR gate is proportion to the sum of the width of pullup transistors and pulldown transistors  $W + 4W = 5W$
- Total input capacitance of an inverter is proportion to  $3W$
- 

- The logical effort  $g_{NOR} = \frac{C_{NOR}}{C_{inv}} = \frac{5}{3}$







- Normalized delay:

$$d = f + p$$

- Stage effort ( $f$ ) depends on the load
- Intrinsic delay ( $p$ ) of the logic gate
- Stage effort ( $f$ )
  - Logical effort ( $g$ )

$$g = \frac{C_{gate}}{C_{inv}}$$

- Electrical effort ( $h$ )

$$h = \frac{C_{in\ of\ load}}{C_{in\ of\ inv}}$$

- Stage effort

$$f = gh$$





- Multistage logic network:
- Normalized path delay

$$D = NF^{\frac{1}{N}} + P$$

- Parasitic path delay  $P$ .
- Path logical effort  $G$  (the product of the individual logical efforts of the gates).
- Path electrical effort  $H$  is the ratio of the load of the path to its input.

$$F = GH$$

- Path branching effort  $B$  is product of individual path effort.

$$F = GHB$$





- Minimum delay:

$$f = F^{\frac{1}{N}}$$

- Number of stage N.
- Total normalized delay of an inverter

$$d = gh + p = (1)(1) + 1 = 2$$

- Normalized parasitic delay of 2-input NAND gate

$$d = gh + p = \left(\frac{4}{3}\right)(1) + 2 = \frac{10}{3}$$

- Normalized parasitic delay of 2-input NOR gate

$$d = gh + p = \left(\frac{5}{3}\right)(1) + 2 = \frac{11}{3}$$



- Logic Gates

Gate Type	Logic Effort	Formula	$n = 2$ $\gamma = 2$	$n = 3$ $\gamma = 2$	$n = 4$ $\gamma = 2$
NAND	Total	$\frac{n(n + \gamma)}{1 + \gamma}$	$\frac{8}{3}$	5	8
	per input	$\frac{(n + \gamma)}{1 + \gamma}$	$\frac{4}{3}$	$\frac{5}{3}$	2
NOR	Total	$\frac{n(n + \gamma)}{1 + \gamma}$	$\frac{10}{3}$	7	12
	per input	$\frac{(n + \gamma)}{1 + \gamma}$	$\frac{5}{3}$	$\frac{7}{3}$	3



- Logic Gates

Gate Type	Logic Effort	Formula	$n = 2$ $\gamma = 2$	$n = 3$ $\gamma = 2$	$n = 4$ $\gamma = 2$
XOR XNOR	Total	$n^2 (2^{n-1})$	8	36	128
	per boundle	$n (2^{n-1})$	4	12	32
MUX	Total	$4n$	8	12	16
	d, s*	2, 2	2, 2	2, 2	2, 2